

IN THE SPECIFICATION

Please amend the paragraph beginning at page 16, line 27 to page 17, line 8, as follows:

Next, an explanation will be ~~give~~ given of a method of processing semiconductor wafers 10 in the heat-processing apparatus 1 described above. This embodiment is exemplified by a case where a titanium nitride film is formed on the wafers 10, with reference to the recipe shown in FIG. 2. The operations described below of respective portions of the heat-processing apparatus 1 are controlled by the control section 21.